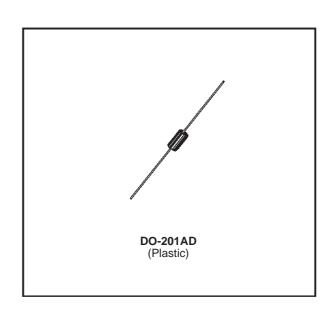


BYT 13-600 →1000

FAST RECOVERY RECTIFIER DIODES

- SOFT RECOVERY
- VERY HIGH VOLTAGE
- SMALL RECOVERY CHARGE



APPLICATIONS

- ANTISATURATION DIODES FOR TRANSIS-TOR BASE DRIVE
- SNUBBER DIODES

ABSOLUTE MAXIMUM RATINGS (limiting values)

Symbol	Parameter	Value	Unit			
I _{FRM}	Repetive Peak Forward Current	$t_p \le 20 \mu s$	50	Α		
I _{F (AV)}	Average Forward Current *	$T_a = 55^{\circ}C$ $\delta = 0.5$	3	А		
I _{FSM}	Surge non Repetitive Forward Current	t _p = 10ms Sinusoidal	100	А		
P _{tot}	Power Dissipation *	3.75	W			
T _{stg} T _j	Storage and Junction Temperature Range - 40 to + 150 - 40 to + 150					
TL	Maximum Lead Temperature for Soldering during 10s at 4mm 230 from Case					

Symbol	Parameter		Unit			
Cyllibol	T di diffetei	600	800	1000	"	
V_{RRM}	Repetitive Peak Reverse Voltage	600	800	1000	V	

THERMAL RESISTANCE

Symbol	Parameter	Value	Unit
R _{th (j - a)}	Junction-ambient*	25	°C/W

^{*} On infinite heatsink with 10mm lead length.

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ELECTRICAL CHARACTERISTICS

STATIC CHARACTERISTICS

Synbol	Test Conditions	Min.	Тур.	Max.	Unit
I_R	$T_j = 25^{\circ}C$ $V_R = V_{RRM}$			20	μΑ
V _F	$T_j = 25^{\circ}C$ $I_F = 3A$			1.3	٧

RECOVERY CHARACTERISTICS

Symbol		Test	Min.	Тур.	Max.	Unit		
t _{rr}	T _j = 25°C	$I_F = 0.5A$	$I_R = 1A$	$I_{rr} = 0.25A$			150	ns

To evaluate the conduction losses use the following equations:

 $V_F = 0.95 + 0.050 I_F$

 $P = 0.95 \times I_{F(AV)} + 0.050 I_{F^{2}(RMS)}$

Figure 1. Maximum average power dissipation versus average forward current.

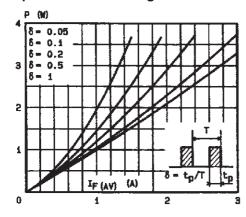


Figure 2. Average forward current versus ambient temperature.

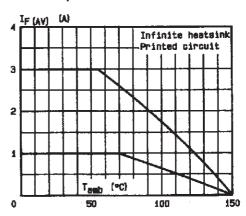
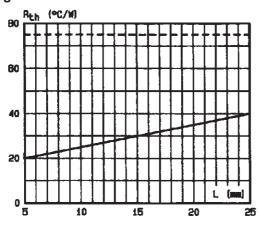
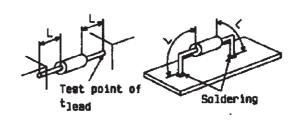


Figure 3. Thermal resistance versus lead length.



Mounting n°1 INFINITE HEATSINK

Mounting n°2 PRINTED CIRCUIT



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Figure 4. Transient thermal impedance junction-ambient for mounting n^2 versus pulse duration (L = 10 mm).

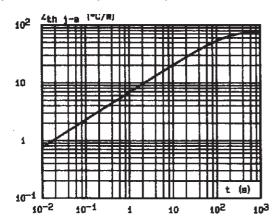


Figure 5. Peak forward current versus peak forward voltage drop (maximum values).

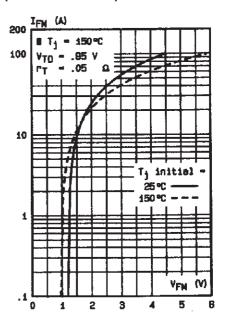


Figure 6. Capacitance versus reverse applied voltage

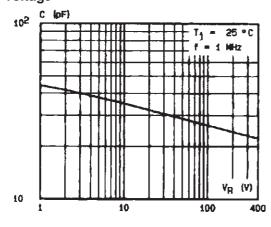
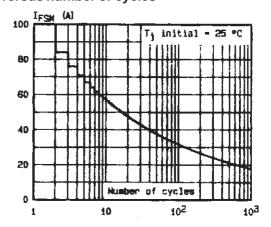
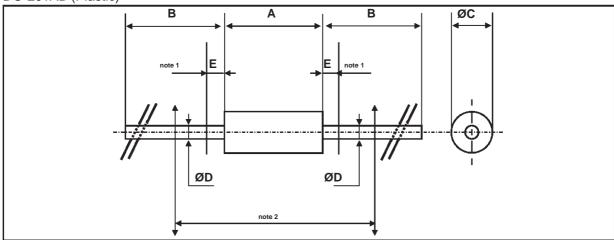


Figure 7. Non repetitive surge peak current versus number of cycles



PACKAGE MECHANICAL DATA

DO-201AD (Plastic)



REF.	DIMENSIONS				NOTES
	Millin	neters Inches		hes	
	Min.	Max.	Min.	Max.	
Α		9.50		0.374	1 - The lead diameter Ø D is not controlled over zone E
В	25.40		1.000		
ØC		5.30		0.209	2 - The minimum axial lengh within which the device may be placed with its leads bent at right angles is 0.59"(15 mm)
Ø D		1.30		0.051	
Е		1.25		0.049	

■ Marking : type number, white band indicates cathode

■ Cooling method: by convection (method A)

■ Weight : 1.166g

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